

DATA SHEET

MMBT2907A

GENERAL PURPOSE TRANSISTOR PNP

VOLTAGE -60 Volts **POWER** 300 mW

FEATURES

- HIGH DC CURRENT GAIN.
- LOW COLLECTOR-EMITTER SATURATION VOLTAGE BOTH NORMAL AND Pb-FREE PACKAGE ARE AVAILABLE.
- LEAD FREE AND HALOGEN-FREE

MECHANICAL DATA

- CASE : SOT-23
- TERMINAL : SOLDERABLE PER MIL-STD-202, METHOD 208
- APPROX. WEIGHT:0.008GRAM



CASE : SOT-23

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

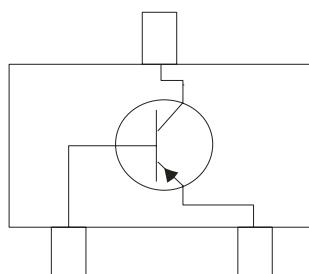
RATINGS AT 25°C AMBIENT TEMPERATURE UNLESS OTHERWISE SPECIFIED.

| PARAMETER | SYMBOL | MMBT2907A | UNITS |
|--|----------------|--------------|-------|
| COLLECTOR-EMITTER VOLTAGE | V_{CEO} | -60 | V |
| COLLECTOR-BASE VOLTAGE | V_{CBO} | -60 | V |
| EMITTER-BASE VOLTAGE | V_{EBO} | -5.0 | V |
| COLLECTOR CURRENT-CONTINUOUS | I_C | -600 | mA |
| POWER DISSIPATION @ $T_A = 25^\circ C$ | P_D | 300 | mW |
| OPERATING AND STORAGE JUNCTION TEMPERATURE RANGE | T_J, T_{STG} | - 55 TO +150 | °C |

NOTE:

1. Indicates Data in addition to JEDEC Requirements.

P N P



ELECTRICAL CHARACTERISTICS

ELECTRICAL CHARACTERISTICS (AT $T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

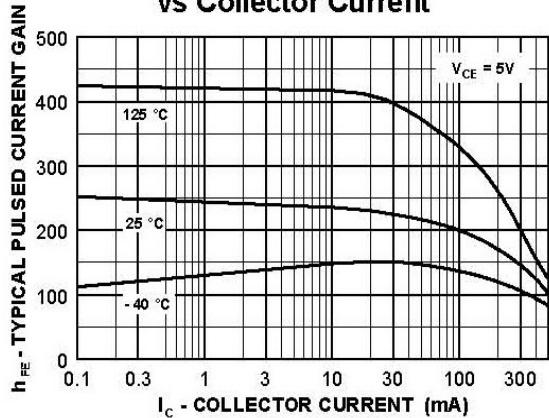
| CHARACTERISTIC | SYMBOL | TEST CONDITIONS | MIN. | MAX. | UNITS |
|--|---------------|---|------|------|---------|
| OFF CHARACTERISTICS | | | | | |
| Collector-Emitter Breakdown Voltage (Note.1) | $V_{(BR)CEO}$ | $I_C = -10mA, I_B = 0$ | -60 | - | V |
| Collector-Base Breakdown Voltage | $V_{(BR)CBO}$ | $I_C = -10\mu A, I_E = 0$ | -60 | - | V |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | $I_E = -10\mu A, I_C = 0$ | -5.0 | - | V |
| Emitter cut-off Current | I_{EBO} | $V_{EB} = -3V, I_C = 0$ | - | -0.1 | μA |
| Collector Cut-off Current | I_{CBO} | $V_{CB} = -50V, I_E = 0$ | - | -0.1 | μA |
| Collector Cut-off Current | I_{CEO} | $V_{CE} = -3V, I_B = 0$ | - | -0.1 | μA |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain | h_{FE} | $V_{CE} = -10V, I_C = -0.1mA$ | 75 | - | - |
| | | $V_{CE} = -10V, I_C = -1.0mA$ | 100 | - | |
| | | $V_{CE} = -10V, I_C = -10mA$ | 100 | - | |
| | | $V_{CE} = -10V, I_C = -150mA$ | 100 | 300 | |
| | | $V_{CE} = -10V, I_C = -500mA$ | 50 | - | |
| Collector-Emitter Saturation Voltage | $V_{CE(SAT)}$ | $I_C = -150mA, I_B = -15mA$ | - | -0.4 | V |
| | | $I_C = -500mA, I_B = -50mA$ | - | -1.6 | |
| Base-Emitter Saturation Voltage | $V_{BE(SAT)}$ | $I_C = -150mA, I_B = -15mA$ | - | -1.3 | V |
| | | $I_C = -500mA, I_B = -50mA$ | - | -2.6 | |
| SMALL-SIGNAL CHARACTERISTICS | | | | | |
| Current-Gain-Bandwidth Product | f_T | $I_C = -50mA, V_{CE} = -20V, f = 100 MHz$ | 200 | - | MHz |
| Delay Time | t_d | $V_{CC} = -30V, I_C = -150mA, I_{B1} = I_{B2} = -15mA$ | - | 10 | μS |
| Rise Time | t_r | | | 40 | μS |
| Storage Time | t_s | $V_{CC} = -6.0V, I_C = -150mA, I_{B1} = I_{B2} = -15mA$ | - | 80 | μS |
| Fall Time | t_f | | | 30 | μS |

NOTE:

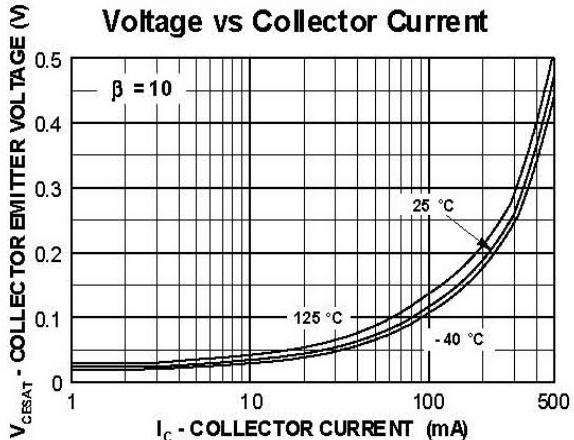
1.Pulse Test: Pulse Width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$.



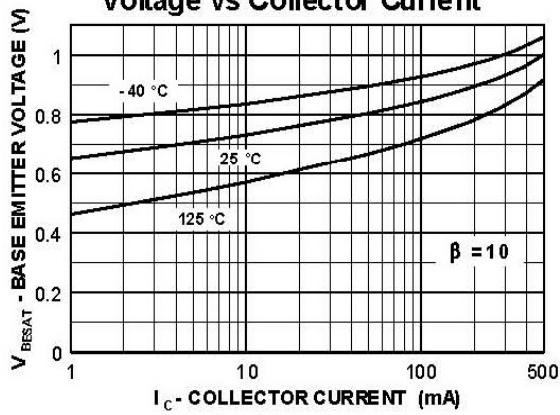
**Typical Pulsed Current Gain
vs Collector Current**



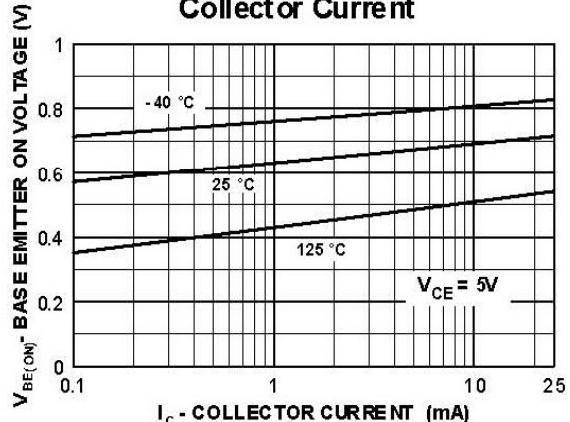
**Collector-Emitter Saturation
Voltage vs Collector Current**



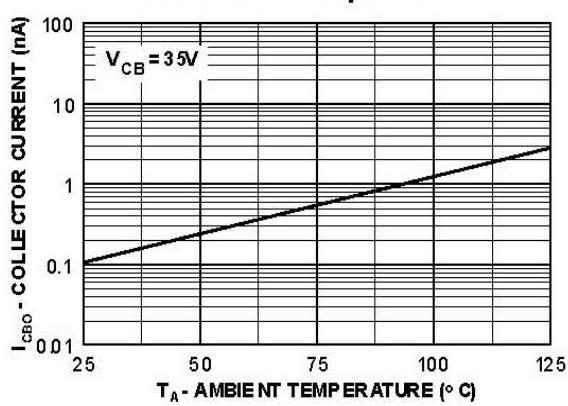
**Base-Emitter Saturation
Voltage vs Collector Current**



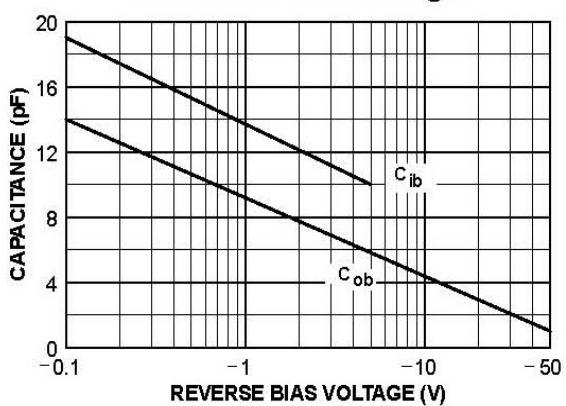
**Base Emitter ON Voltage vs
Collector Current**



**Collector-Cutoff Current
vs Ambient Temperature**

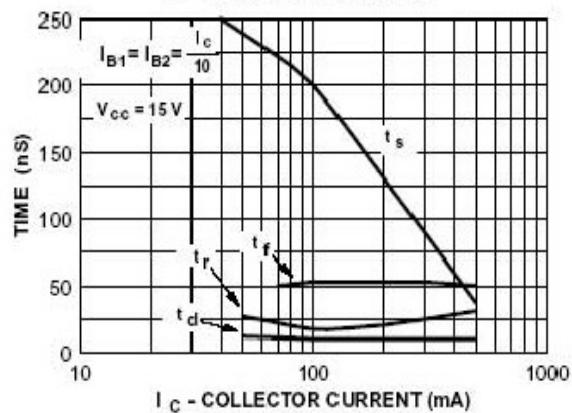


**Input and Output Capacitance
vs Reverse Bias Voltage**

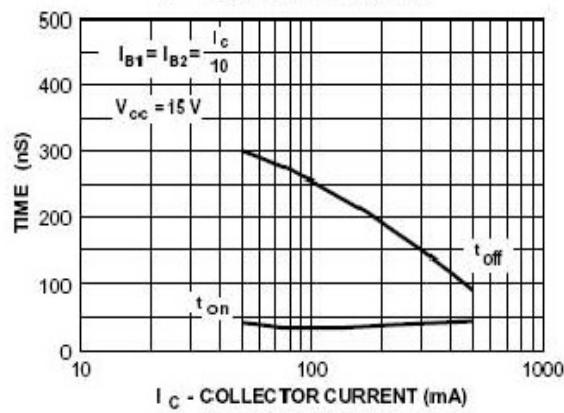




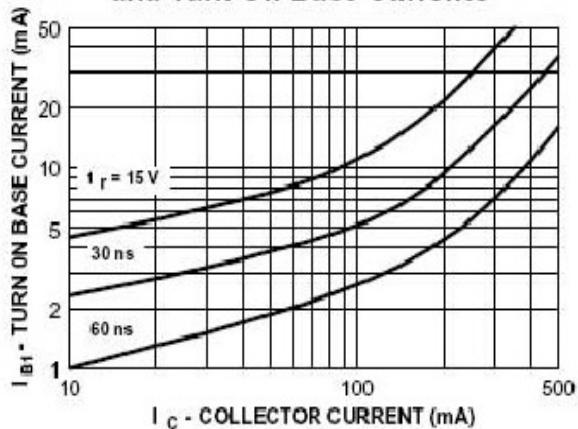
Switching Times vs Collector Current



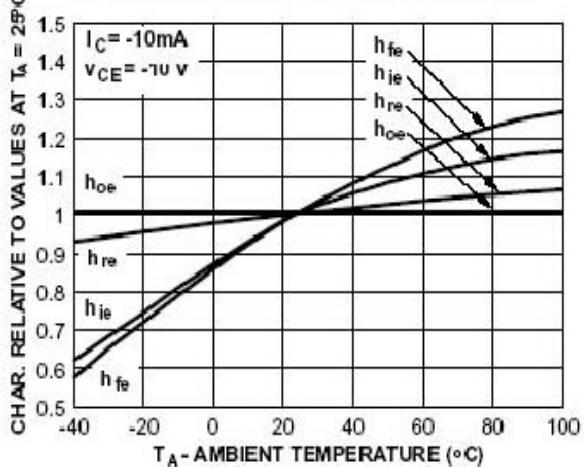
Turn On and Turn Off Times vs Collector Current



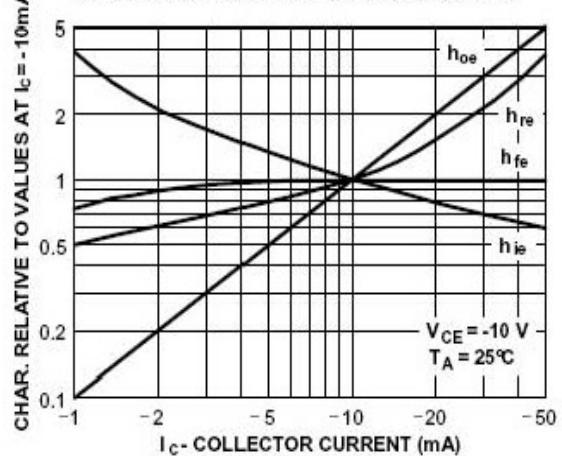
Rise Time vs Collector and Turn On Base Currents



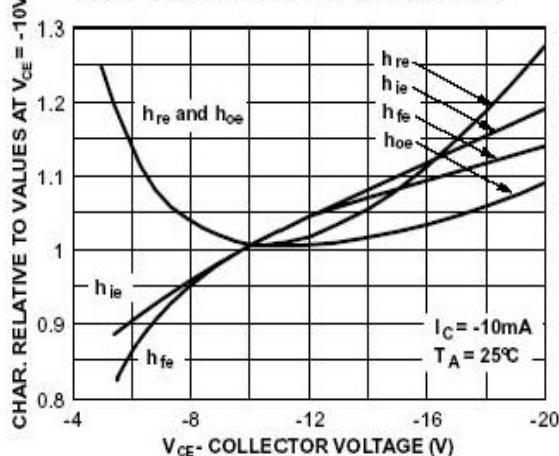
Common Emitter Characteristics



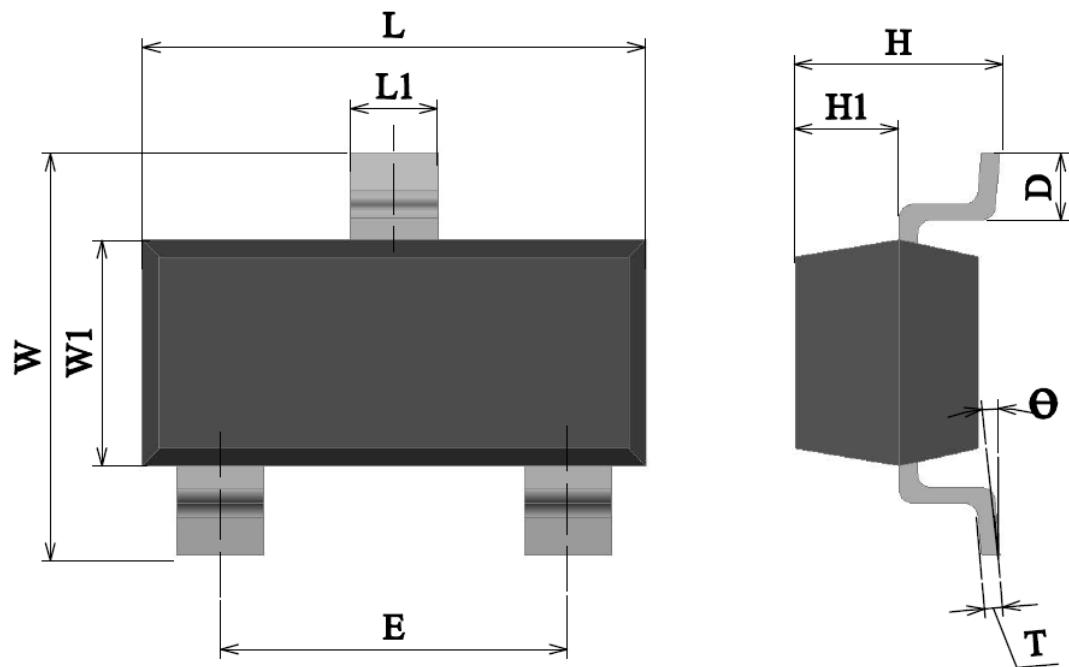
Common Emitter Characteristics



Common Emitter Characteristics



SOT-23 DIMENSION



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|-----------|---------------------------|------|----------------------|-------|
| | Min | Max | Min | Max |
| L | 2.80 | 3.10 | 0.110 | 0.122 |
| L1 | 0.30 | 0.50 | 0.012 | 0.020 |
| W | 2.25 | 2.54 | 0.089 | 0.100 |
| W1 | 1.20 | 1.40 | 0.047 | 0.055 |
| E | 1.80 | 2.00 | 0.071 | 0.079 |
| H | 0.90 | 1.15 | 0.035 | 0.045 |
| H1 | 0.40 | 0.80 | 0.016 | 0.031 |
| D | 0.30 | 0.50 | 0.012 | 0.020 |
| T | 0.08 | 0.15 | 0.003 | 0.006 |
| Θ | 0° | 8° | 0 ° | 8 ° |

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